





PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	:	MICRON TECHNOLOGY, INC.)
App. No.	:	listed below)
Filed	:	listed below)
For	**	listed below)
Examiner	:	Unknown)

ESTABLISHMENT OF RIGHT OF ASSIGNEE TO TAKE ACTION AND REVOCATION AND POWER OF ATTORNEY

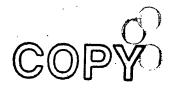
United States Patent and Trademark Office P.O. Box 2327 Arlington, VA 22202

Dear Sir:

The undersigned is empowered to act on behalf of the assignee below (the "Assignee") for the cases listed below. The original Assignment from Honeywell, Inc. to Micron Technology, Inc. is recorded at Reel 012188 and Frame 0697, and each of the listed cases was previously assigned of record to Honeywell, Inc.:

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09/318,073	MICRON.196CP1	Local Shielding For Memory Cells	PENDING	009993/0887
09/618,237	MICRON.211A	Magneto-Resistive Memory Array	PENDING	011267/0257
09/618,256	MICRON.210A	Magneto-Resistive Memory Having Sense Amplifier With Offset Control	PENDING	011430/0400
09/618,492	MICRON.212A	Memory Redundancy With Programmable Non-Volatile Control	PENDING	011377/0194
09/618,504	MICRON.198A	MRAM Architectures For Increased Write Selectivity	PENDING	012188/0697
09/638,415	MICRON.213A	Magneto-Resistive Memory With Shared Wordline And	PENDING	011189/0647

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Sense Line White North Contact Miles Terrent Social Strategic intention REGALLEGIA 09/638,419 MICRON.214A Passivated Magneto-Resistive **PENDING** 011287/0078 Bit Structure And Passivation Method Therefor 09/638,637 MICRON.215A Pulsed Write Techniques For PENDING 011262/0993 Magneto-Resistive Memories 09/668,922 MICRON.216A Shielding Arrangement To **PENDING** 011199/0931 Protect A Circuit From Stray Magnetic Fields 08/962,512 MICRON.197A Shielded Package For Magnetic 5,939,772 9147/0852 **Devices** 08/993,009 MICRON.196A Self-Aligned Wordline Keeper 5,956,267 8940/0969 And Method Of Manufacture Therefor -08/962,518 MICRON.208A MRAM Design To Reduce 5,982,658 9066/0083 Dissimilar Nearest Neighbor **Effects** 08/940,587 MICRON.207A Method To Permit High 6,027,948 N/A Temperature Assembly **Processes For Magnetically** Sensitive Devices 08/993,005 MICRON.209A Method Of Manufacturing A 6,048,739 8940/0979 High Density Magnetic Memory Device 09/365,308 MICRON.206A Method And Apparatus For 6,134,138 010147/0942 Reading A Magneto-Resistive Memory 09/396,189 MICRON.185DV1 Non-Volatile Storage Latch 6,147,922 9115/0907 09/429/664 MICRON.185CP1 Non-Volatile Storage Latch 6,175,525 010353/0253 09/455,850 MICRON.199A Method And Apparatus For 6,178,111 010477/0485 Writing Data States To Non-Volatile Storage Devices 09/059,871 MICRON.185A Non-Volatile Storage Latch 6,269,027 9115/0907 06/879,679 MICRON.189A Magneto-Resistive Memory 4,731,757 4574/0767 Including Think Film Storage Cells Having Tapered Ends 06/908,075 MICRON.187A Differential Arrangement 4,751,677 4604/0016 Magnetic Memory Cell 07/008,211 MICRON.195A Vialess Shorting Bars For 4,754,431 4664/0251 Magneto-Resistive Devices 06/870,068 MICRON.188A Magneto-Resistive Memory 4,780,848 4559/0920 With Multi-Layer Storage Cells

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07/078,612	MICRON.186A	Differential Magneto-Resistive Memory Sensing	4,829,476	4748/0535
07/168,293	MICRON.192DV1 MICRON.195DV1	Vialess Shorting Bars For Magneto-Resistive Devices	4,897,288	4664/0251
07/161,534	MICRON.194A	Magnetic Device Integrated Circuit Interconnection System	4,918,655	4838/0775
07/404,003	MICRON.203FW1	Semiconductor Device Housing With Magnetic Field Protection	4,953,002	4896/0504
07/504,777	MICRON.191A	Opposed Field Magneto- Resistive Memory Sensing	5,012,444	5269/0357
07/505,090	MICRON.190A	Magnetic State Entry Assurance	5,060,193	5275/0230
07/507,682	MICRON.193A	Inductively Sensed Magnetic Memory	5,064,499	5283/0794
08/061,603	MICRON.202A	Sense Amplifier Input Stage For Single Array Memory	5,349,302	6564/0073
08/365,852	MICRON.204A	Highly Producible Magneto- Resistive RAM Process	5,496,759	7300/0805
08/576,279	MICRON.205A	Integrated Spacer For Magneto- Resistive RAM	5,569,617	7822/0914
08/576,732	MICRON.200A	Magnetic Hardening Of Bit Edges Of Magneto-Resistive RAM	5,756,366	7807/0166

The original assignment from Honeywell, Inc. to Micron Technology, Inc. is recorded at Reel 012188 and Frame 0697. These assignments represents the entire chain of title of these inventions from the Inventors to the Assignee.

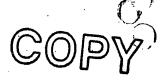
I declare that all statements made herein are true, and that all statements made upon information and belief are believed to be true, and further, that these statements were made with the knowledge that willful, false statements and the like so made are punishable by fine or imprisonment, or both, under 18 U.S.C. § 1001, and that willful, false statements may jeopardize the validity of the application, or any patent issuing thereon.

The undersigned hereby revokes any previous powers of attorney in the subject application, and hereby appoints the registrants of Knobbe, Martens, Olson & Bear, LLP, 620 Newport Center Drive, Sixteenth Floor, Newport Beach, California 92660, Telephone (949) 760-0404, Customer No. 20,995, and Michael L. Lynch, Reg. No. 30,871, Micron Technology, Inc., 8000 South Federal Way, P.O. Box 6, Boise, ID 83707-0006, as its attorneys

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with full power of substitution and revocation to prosecute this application and to transact all business in the U.S. Patent and Trademark Office connected herewith. This appointment is to be to the exclusion of the inventor(s) and his attorney(s) in accordance with the provisions of 37 C.F.R. § 3.71.

Please use Customer No. 20,995 for all communications.

MICRON TECHNOLOGY. INC.

Dated: February 28, 2002

By: Roderic Lewis

Vice President of Legal Affairs, General Counsel and Corporate Secretary

Address: 8000 South Federal Way

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